**Vishay Siliconix** 

### Precision Monolithic Quad SPST Low-Voltage CMOS Analog Switches

#### DESCRIPTION

SHAY

The DG441L, DG442L are low voltage pin-for-pin compatible companion devices to the industry standard DG441L, DG442L with improved performance.

Using BiCMOS wafer fabrication technology allows the DG441L, DG442L to operate on single and dual supplies. Single supply voltage ranges from 3 V to 12 V while dual supply operation is recommended with  $\pm$  3 V to  $\pm$  6 V.

Combining high speed (t<sub>ON</sub>: 20 ns), flat R<sub>DS(on)</sub> over the analog signal range (5  $\Omega$ ), minimal insertion lose (- 3 dB at 280 MHz), and excellent crosstalk and off-isolation performance (- 50 dB at 50 MHz), the DG441L, DG442L are ideally suited for audio and video signal switching.

The DG441L, DG442L responds to opposite control logic as shown in the Truth Table open and two normally closed switches.

### **FEATURES**

- Halogen-free according to IEC 61249-2-21 Definition
- 2.7 V thru 12 V single supply or ± 3 V thru ± 6 V dual supply
- On-resistance R<sub>DS(on)</sub>: 17 Ω
- Fast switching t<sub>ON</sub>: 20 ns - t<sub>OFF</sub>: 12 ns
- TTL, CMOS compatible
- Low leakage: 0.25 nA
- 2000 V ESD protection
- Compliant to RoHS Directive 2002/95/EC

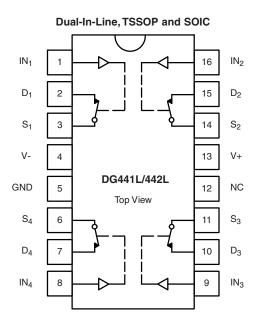
#### BENEFITS

- Widest dynamic range
- Low signal errors and distortion
- Break-before-make switching action
- Simple interfacing

#### **APPLICATIONS**

- Precision automatic test equipment
- Precision data acquisition
- Communication systems
- Battery powered systems
- Computer peripherals
- SDSL, DSLAM
- Audio and video signal routing

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE								
Logic	DG441L	DG442L						
0	On	Off						
1 Off On								

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

ORDERING INFORMATION								
Temp. Range	Package	Part Number						
	16-pin TSSOP	DG441LDQ-T1-E3						
- 40 °C to 85 °C	10-pin 1330F	DG442LDQ-T1-E3						
- 40 0 10 85 0	16-pin narrow	DG441LDY-T1-E3						
	SOIC	DG442LDY-T1-E3						
	16 pip CorDIP	DG441LAK, DG441LAK/883						
- 55 °C to 125 °C	16-pin CerDIP	DG442LAK, DG442LAK/883						
- 55 0 10 125 0	LCC-20	DG441LAZ/883						
	LCC-20	DG442LAZ/883						

Document Number: 71399 S11-1066-Rev. E, 30-May-11 www.vishay.com

HALOGEN

FREE

Vishay Siliconix



### **ABSOLUTE MAXIMUM RATINGS** ( $T_A = 25 \,^{\circ}$ C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
V + to V -			- 0.3 to 13	
GND to V - A			7	v
Digital Inputs <sup>a</sup> V <sub>S</sub> , V <sub>D</sub>			GND - 0.3 to (V +) + 0.3 or 30 mA, whichever occurs first	
Continuous Current (any terminal)			30	mA
Current, S or D (pulsed 1 ms, 10 % duty cycle)			100	IIIA
Storage Temperature	(DQ, DY suffix)		- 65 to 125	°C
Storage temperature	(AK suffix)		- 65 to 150	
	16-pin TSSOP <sup>c</sup>		450	
Power Dissipation (Packages) <sup>b</sup>	16-pin narrow Body SOIC <sup>d</sup>		650	mW
	16-pin CerDIP <sup>e</sup>		900	

Notes:

a. Signals on  $S_X$ ,  $D_X$ , or  $IN_X$  exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC board.

c. Derate 7 mW/°C above 75 °C d. Derate 7.6 mW/°C above 75 °C

e. Derate 12 mW/°C above 75 °C.

SPECIFICATIONS <sup>a</sup> (Single Supply 12 V)										
		Test Conditions Unless Otherwise Specified V + = 12 V, V - = 0 V			A Suffix Limits - 55 °C to 125 °C		D Suffix - 40 °C	to 85 °C	Unit	
Parameter	Symbol	V = 12 V, V = 0 V $V_{IN} = 2.4 V, 0.8 V^{f}$	Temp. <sup>b</sup>	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	onic	
Analog Switch				1			1			
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		0	12	0	12	V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V + = 10.8 V, V - = 0 V $I_{S} = 10 mA, V_{D} = 2/9 V$	Room Full	20		30 45		30 40	0	
On-Resistance Match Between Channels <sup>e</sup>	$\Delta R_{DS(on)}$	I <sub>S</sub> = 10 mA, V <sub>D</sub> = 9 V	Room	0.1		0.5		0.5	Ω	
Switch Off Leakage Current	I <sub>S(off)</sub>	V <sub>D</sub> = 1/11 V, V <sub>S</sub> = 11/1 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10		
Switch On Leakage Suitchit	I <sub>D(off)</sub>		Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA	
Channel On Leakage Current	I <sub>D(on)</sub>	$V_{S} = V_{D} = 11/1 V$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10		
Digital Control										
Input Current, V <sub>IN</sub> Low	۱ <sub>IL</sub>	V <sub>IN</sub> Under Test = 0.8 V	Full	0.01	- 1.5	1.5	- 1	1		
Input Current, V <sub>IN</sub> High	I <sub>IH</sub>	V <sub>IN</sub> Under Test = 2.4 V	Full		- 1.5	1.5	- 1	1	μA	
Dynamic Characteristics										
Turn-On Time	t <sub>ON</sub>	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	Room Full	20		60 80		60 70	ns	
Turn-Off Time	t <sub>OFF</sub>	$\overline{V}_{S} = 5 V$ , see figure 2	Room Full	12		35 50		35 45	ns	
Charge Injection <sup>e</sup>	Q	$V_{g}$ = 0 V, $R_{g}$ = 0 $\Omega$ , $C_{L}$ = 10 nF	Room	5					рС	
Off Isolation <sup>e</sup>	OIRR	$R_1 = 50 \Omega$ , $C_1 = 5 pF$ , f = 1 MHz	Room	71					dB	
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$n_{\rm L} = 30.32, 0_{\rm L} = 3.01, 1 = 1.0012$	Room	95					uБ	
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	5						
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz	Room	6					pF	
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	15						
Power Supplies	•			1				<u> </u>		
Positive Supply Current	l+		Full	0.03		1.5		1		
Negative Supply Current	I-	V <sub>IN</sub> = 0 V or 12 V	Room Full	- 0.002	- 1 - 7.5		- 1 - 5		μA	
Ground Current	I <sub>GND</sub>		Full	_ 0.002	- 1.5		- 1			

www.vishay.com 2

Document Number: 71399 S11-1066-Rev. E, 30-May-11



Vishay Siliconix

SPECIFICATIONS <sup>a</sup> (Dual Supply ± 5 V)									
		Test Conditions Unless Otherwise Specified			A Suffix Limits - 55 °C to 125 °C			<b>to 85 °C</b>	Unit
Parameter	Symbol	V + = 5 V, V - = -5 V $V_{IN} = 2.4 V, 0.8 V^{f}$	Temp. <sup>b</sup>	Тур. <sup>с</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	onit
Analog Switch									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		- 5	5	- 5	5	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V + = 5 V, V - = - 5 V $I_S$ = 10 mA, V <sub>D</sub> = ± 3.5 V	Room Full	20		33 45		33 40	Ω
On-Resistance Match Between Channels <sup>e</sup>	$\Delta R_{DS(on)}$	$I_{\rm S} = 10 \text{ mA}, V_{\rm D} = \pm 3.5 \text{ V}$	Room	0.1		0.5		0.5	22
Switch Off	I <sub>S(off)</sub>	V + = 5.5 , V - = - 5.5 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Leakage Current <sup>g</sup>	I <sub>D(off)</sub>		Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current <sup>g</sup>	I <sub>D(on)</sub>	V + = 5.5 V, V - = -5.5 V $V_{S} = V_{D} = \pm 4.5 V$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control									
Input Current, V <sub>IN</sub> Low <sup>e</sup>	I <sub>IL</sub>	V <sub>IN</sub> Under Test = 0.8 V	Full	0.05	- 1.5	1.5	- 1	1	
Input Current, V <sub>IN</sub> High <sup>e</sup>	I <sub>IH</sub>	V <sub>IN</sub> Under Test = 2.4 V	Full	0.05	- 1.5	1.5	- 1	1	μA
Dynamic Characteristics									
Turn-On Time	t <sub>ON</sub>	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	Room Full	21		60 83		60 70	ns
Turn-Off Time	t <sub>OFF</sub>	$V_{S} = \pm 3.5 V$ , see figure 2	Room Full	16		35 55		35 45	115
Charge Injection <sup>e</sup>	Q	$V_g = 0 V$ , $R_g = 0 \Omega$ , $C_L = 10 nF$	Room	5					рС
Off Isolation <sup>e</sup>	OIRR		Room	68					
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 \ \Omega$ , $C_L = 5 \ pF$ , f = 1 MHz	Room	85					dB
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	9					
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz	Room	9					pF
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	20					
Power Supplies	1			1	1	1		1	-
Positive Supply Current <sup>e</sup>	l+		Full	0.002		1.5		1	
Negative Supply Current <sup>e</sup>	-	V <sub>IN</sub> = 0 V or 5 V	Room Full	- 0.002	- 1 - 7.5		- 1 - 5		μA
Ground Current <sup>e</sup>	I <sub>GND</sub>		Full	- 0.002	- 1.5		- 1		

# Vishay Siliconix



SPECIFICATIONS <sup>a</sup> (Single Supply 5 V)													
		Test Conditions Unless Otherwise Specified								<b>c Limits</b> o 125 °C	<b>D Suffix</b> - 40 °C	to 85 °C	Unit
Parameter	Symbol	V + = 5 V, V - = 0 V V <sub>IN</sub> = 2.4 V, 0.8 V <sup>f</sup>	Temp. <sup>b</sup>	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	om				
Analog Switch													
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full			5		5	V				
Drain-Source On-Resistance <sup>e</sup>	R <sub>DS(on)</sub>	V + = 4.5 V I <sub>S</sub> = 5 mA, V <sub>D</sub> = 1 V, 3.5 V	Room Full	35		50 88		50 75	Ω				
On-Resistance Match Between Channels <sup>e</sup>	$\Delta R_{DS(on)}$	I <sub>S</sub> = 10 mA, V <sub>D</sub> = 3.5 V	Room	0.5		1		1	52				
Dynamic Characteristics													
Turn-On Time <sup>e</sup>	t <sub>ON</sub>	$R_L = 300 \ \Omega, C_L = 35 \ pF$	Room Hot	27		50 90		50 60	ns				
Turn-Off Time <sup>e</sup>	t <sub>OFF</sub>	$V_{S}$ = 3.5 V, see figure 2	Room Hot	15		30 55		30 40	115				
Charge Injection <sup>e</sup>	Q	$V_{g} = 0 V, R_{g} = 0 \Omega, C_{L} = 10 nF$	Room	0.5					рС				
Power Supplies	Power Supplies												
Positive Supply Current <sup>e</sup>	l +		Full	10		200		100					
Negative Supply Current <sup>e</sup>	۱-	V <sub>IN</sub> = 0 V or 5 V	Room Full	- 0.002	- 1 - 7.5		- 1 - 5		μA				
Ground Current <sup>e</sup>	I <sub>GND</sub>		Full	- 10	- 200		- 100						



### **Vishay Siliconix**

SPECIFICATIONS <sup>a</sup> (Single Supply 3 V)									
		Test Conditions Unless Otherwise Specified			A Suffix Limits - 55 °C to 125 °C		D Suffix Limits - 40 °C to 85 °C		Unit
Parameter	Symbol	V + = 3 V, V - = 0 V $V_{IN} = 0.4 V^{f}$	Temp. <sup>b</sup>	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	onit
Analog Switch									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		0	3	0	3	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V + = 2.7 V, V - = 0 V $I_S = 5 mA, V_D = 0.5, 2.2 V$	Room Full	65		80 115		80 100	Ω
On-Resistance Match Between Channels <sup>e</sup>	$\Delta R_{DS(on)}$	I <sub>S</sub> = 5 mA, V <sub>D</sub> = 2.2 V	Room	1		3		3	52
Switch Off	I <sub>S(off)</sub>	V + = 3.3 , V - = 0 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Leakage Current <sup>g</sup>	I <sub>D(off)</sub>	V <sub>D</sub> = 1, 2 V, V <sub>S</sub> = 2, 1 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current <sup>g</sup>	I <sub>D(on)</sub>	V + = 3.3 V, V - = 0 V $V_S = V_D = 1, 2 V$			- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control									
Input Current, V <sub>IN</sub> Low <sup>e</sup>	۱ <sub>IL</sub>	V <sub>IN</sub> under test = 0.4 V	Full	0.005	- 1.5	1.5	- 1	1	
Input Current, V <sub>IN</sub> High <sup>e</sup>	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full	0.005	- 1.5	1.5	- 1	1	μA
Dynamic Characteristics									
Turn-On Time	t <sub>ON</sub>	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	Room Full	50		136 175		136 151	ns
Turn-Off Time	t <sub>OFF</sub>	$V_{S}$ = 1.5 V, see figure 2	Room Full	30		100 140		100 125	115
Charge Injection <sup>e</sup>	Q	$V_g = 0 V$ , $R_g = 0 \Omega$ , $C_L = 10 nF$	Room	1					рС
Off Isolation <sup>e</sup>	OIRR		Room	68					
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 $ Ω, $C_L = 5 $ pF , f = 1 MHz	Room	85					dB
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	6					
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz	Room	6					pF
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	20					

Notes:

a. Refer to PROCESS OPTION FLOWCHART.

b. Room = 25 °C, Full = as determined by the operating temperature suffix.

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.

e. Guaranteed by design, not subject to production test.

f.  $V_{IN}$  = input voltage to perform proper function.

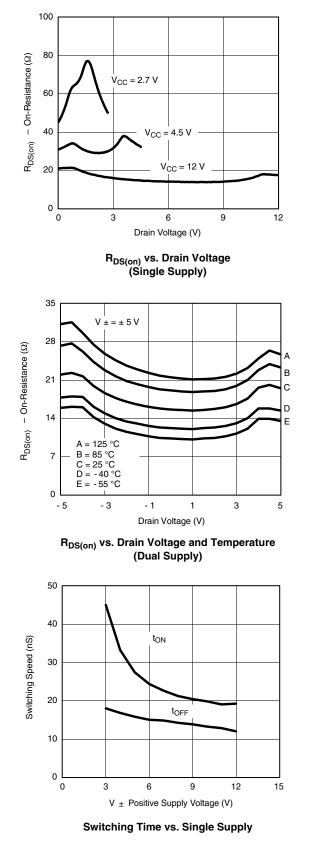
g. Leakage parameters are guaranteed by worst case test conditions and not subject to test.

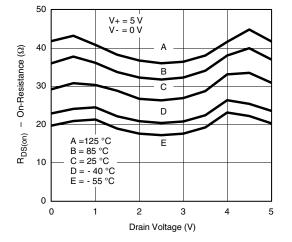
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

VISHAY,

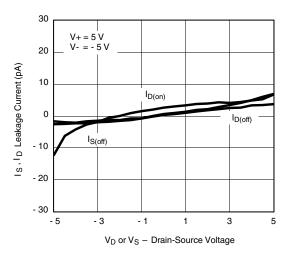
### Vishay Siliconix

### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

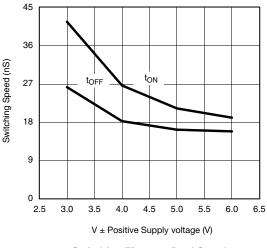




R<sub>DS(on)</sub> vs. Drain Voltage and Temperature (Single Supply)



Leakage Current vs. Analog Voltage (Dual Supply)



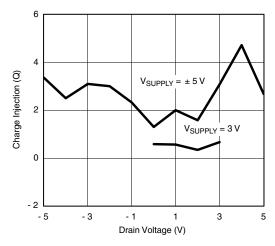
Switching Time vs. Dual Supply

Document Number: 71399 S11-1066–Rev. E, 30-May-11

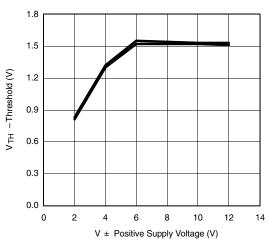


### DG441L, DG442L Vishay Siliconix

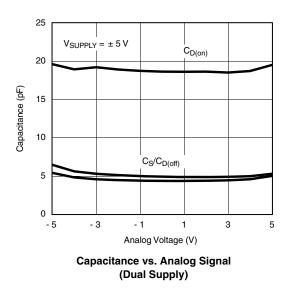
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

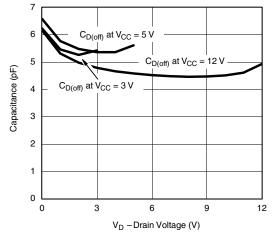


Charge Injection vs. Drain Voltage

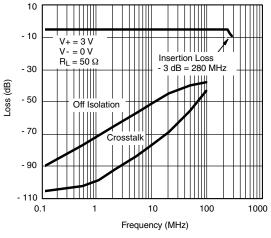


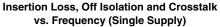
Input Threshold vs. Single Supply Voltage





Drain Capacitance vs. Drain Voltage (Single Supply)





Document Number: 71399 S11-1066–Rev. E, 30-May-11

www.vishay.com

Vishay Siliconix



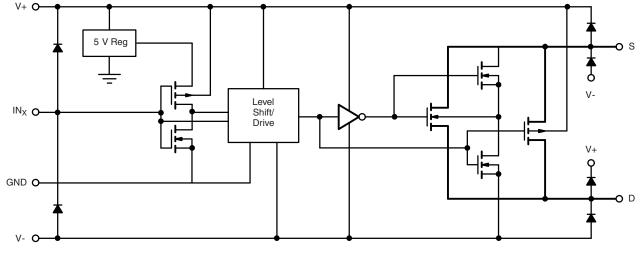
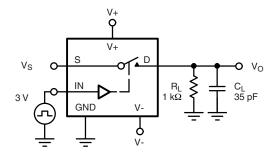
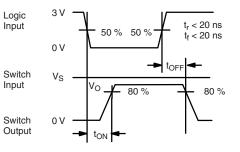


Figure 1.





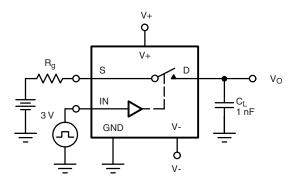
C<sub>L</sub> (includes fixture and stray capacitance)



Logic input waveform is inverted for DG442.

Figure 2. Switching Time

Note:



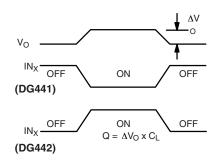


Figure 3. Charge Injection

www.vishay.com 8 Document Number: 71399 S11-1066–Rev. E, 30-May-11

**VISHAY** 



### DG441L, DG442L Vishay Siliconix

### **TEST CIRCUITS**

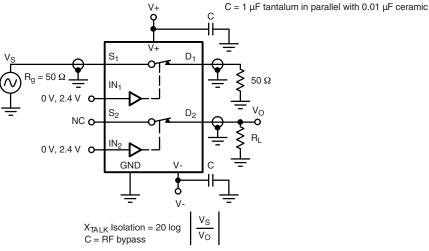
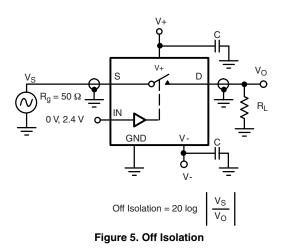


Figure 4. Crosstalk



V+ Q V+ S Meter HP4192A Impedance IN 0 V, 2.4 V O Analyzer or Equivalent D GND v. C Ч-

Figure 6. Source/Drain Capacitances

**Vishay Siliconix** 

### APPLICATIONS

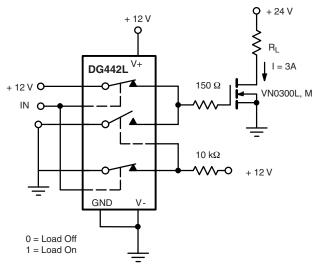
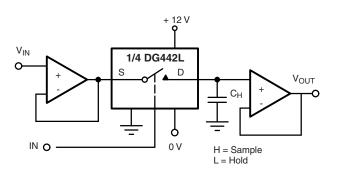
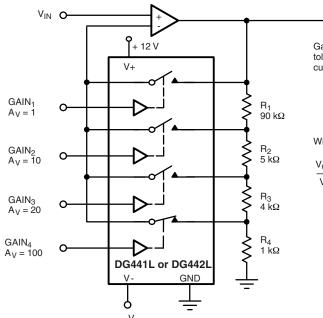


Figure 7. Power MOSFET Driver







Gain error is determined only by the resistor tolerance. Op amp offset and CMRR will limit accuracy of circuit.

With SW<sub>4</sub> Closed

• V<sub>OUT</sub>

$$\frac{OUT}{I_{\rm IN}} = \frac{R_1 + R_2 + R_3 + R_4}{R_4} = 100$$

Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg271399">www.vishay.com/ppg271399</a>.

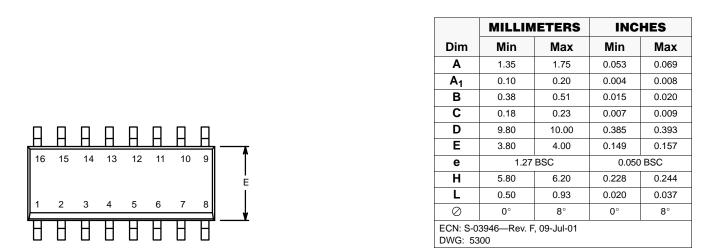
Document Number: 71399 S11-1066–Rev. E, 30-May-11

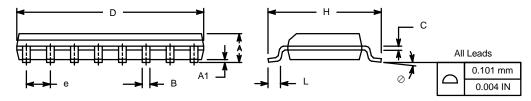




SOIC (NARROW): 16-LEAD

JEDEC Part Number: MS-012



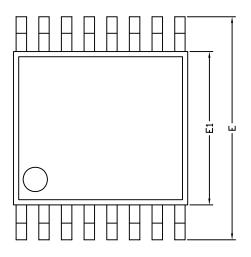


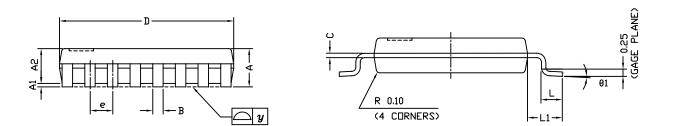


# Package Information

Vishay Siliconix

### TSSOP: 16-LEAD





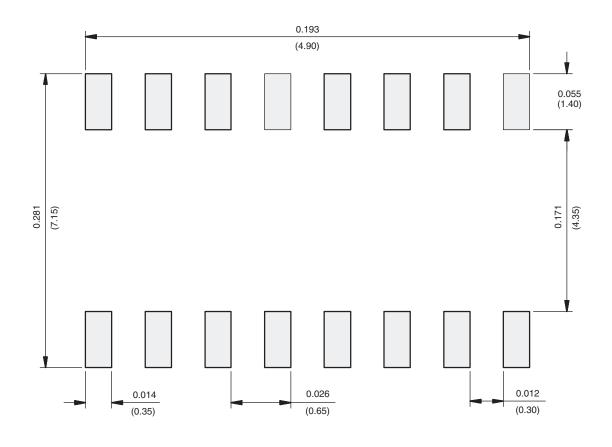
	DIMENSIONS IN MILLIMETERS								
Symbols	Min	Nom	Мах						
A	-	1.10	1.20						
A1	0.05	0.10	0.15						
A2	-	1.00	1.05						
В	0.22	0.28	0.38						
С	-	0.127	-						
D	4.90	5.00	5.10						
E	6.10	6.40	6.70						
E1	4.30	4.40	4.50						
е	-	0.65	-						
L	0.50	0.60	0.70						
L1	0.90	1.00	1.10						
у	-	-	0.10						
θ1	0°	3°	6°						
ECN: S-61920-Rev. D, 23 DWG: 5624	-Oct-06								



**PAD** Pattern

Vishay Siliconix

#### **RECOMMENDED MINIMUM PAD FOR TSSOP-16**



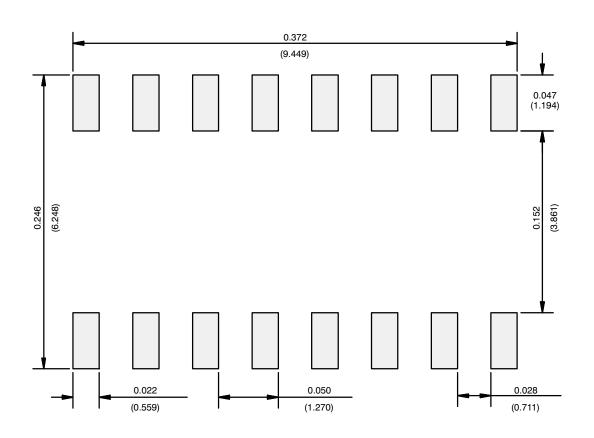
Recommended Minimum Pads Dimensions in inches (mm)

# **Application Note 826**

Vishay Siliconix



### **RECOMMENDED MINIMUM PADS FOR SO-16**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



Vishay

# Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.